BYV29FX-600

Enhanced ultrafast rectifier diode Rev. 01 — 30 June 2009

Product data sheet

1. Product profile

1.1 General description

Enhanced ultrafast epitaxial rectifier diode in a SOD113 (2-lead TO-220F) plastic package.

1.2 Features and benefits

- High thermal cycling performance
- Isolated package
- Low on-state losses

- Low thermal resistance
- Soft recovery characteristic

1.3 Applications

■ Dual Mode (DCM and CCM) PFC

■ Power factor Correction (PFC) for Interleaved Topology

1.4 Quick reference data

Table 1. **Quick reference**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; δ = 0.5; T _h = 72 °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	9	Α
Dynamic	characteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V};$ $dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 5}}{}$	-	17.5	35	ns
Static ch	aracteristics					
V _F	forward voltage	I _F = 9 A; T _j = 150 °C; see <u>Figure 4</u>	-	1.3	1.9	V



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
	K	cathode	отпринов овине	
1			mb	K — A
2	Α	anode		001aaa020
mb	n.c.	mounting base; isolated	SOD113 (TO-220F)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYV29FX-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
$I_{F(AV)}$	average forward current	square-wave pulse; δ = 0.5; T_h = 72 °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	9	Α
I _{FRM}	repetitive peak forward current	square-wave pulse; δ = 0.5; t_p = 25 μ s; T_h = 72 °C	-	18	Α
I _{FSM}	non-repetitive peak	t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C	-	91	Α
	forward current	t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C	-	100	Α

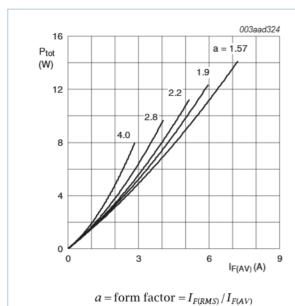


Fig 1. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

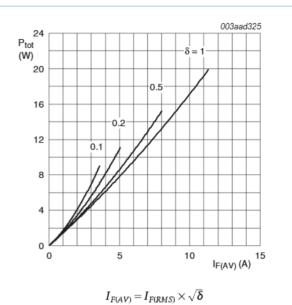


Fig 2. Forward power dissipation as a function of average forward current; square waveform; maximum values

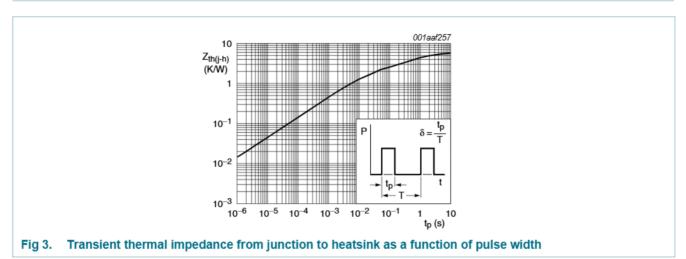
4 of 10

Enhanced ultrafast rectifier diode

Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; see Figure 3	-	-	5.5	K/W
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient free air		-	55	-	K/W



Isolation characteristics

Isolation characteristics Table 6.

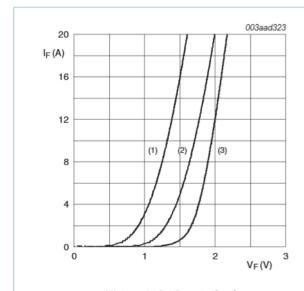
Product data sheet

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	f = 1 MHz; RH = 65 %; between all pins and external heatsink	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	pF

Characteristics

Table 7. Characteristics

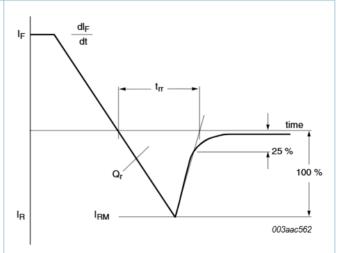
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static cha	Static characteristics						
V_{F}	forward voltage	$I_F = 9 \text{ A}$; $T_j = 25 \text{ °C}$; see Figure 4	-	1.4	2.1	V	
		$I_F = 9 \text{ A}; T_j = 150 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 4}}{}$	-	1.3	1.9	V	
I_R	reverse current	$V_R = 600 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	1.5	mA	
		$V_R = 600 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	50	μΑ	
Dynamic	characteristics						
Q_{Γ}	recovered charge	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A}/\mu\text{s}$; see Figure 5	-	13	-	nC	
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 5	-	17.5	35	ns	
I_{RM}	peak reverse recovery current	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A}/\mu\text{s}$; see Figure 5	-	1.5	-	Α	
V_{FR}	forward recovery voltage	$I_F = 1 \text{ A}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; see Figure 6	-	3.2	-	V	



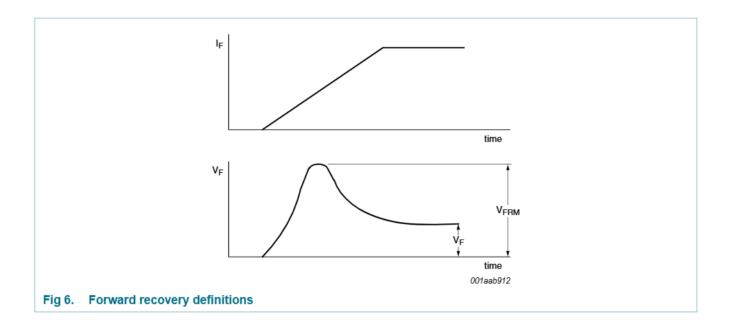
(1) $T_f = 150$ °C; typical values (2) $T_j = 150$ °C; maximum values

(3) $T_i = 25$ °C; maximum values

Fig 4. Forward current as a function of forward voltage



Reverse recovery definitions; ramp recovery



Package outline

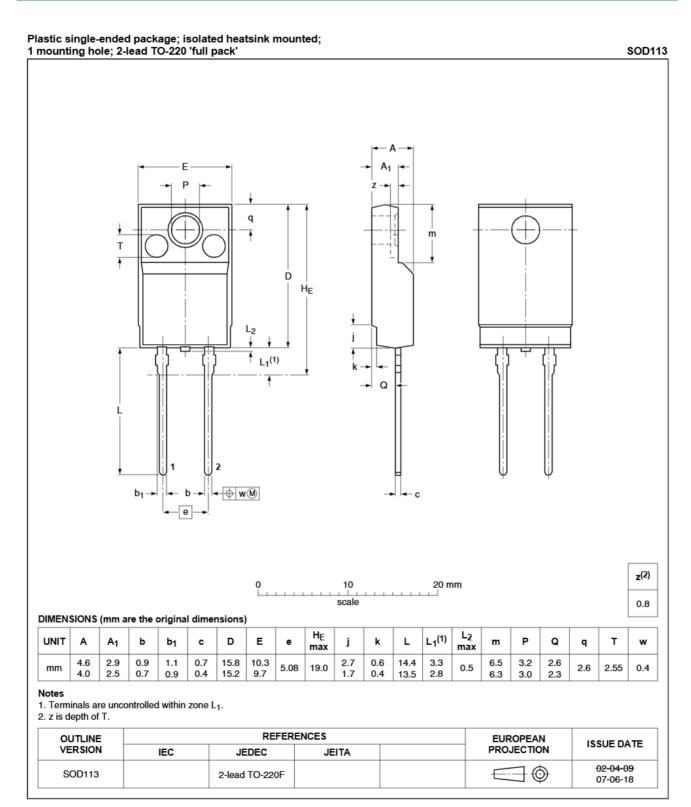


Fig 7. Package outline SOD113 (TO-220F)



8 of 10

Enhanced ultrafast rectifier diode

Revision history

Table 8. **Revision history**

Product data sheet

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV29FX-600_1	20090630	Product data sheet	-	-

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10.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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12. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data1
2	Pinning information2
3	Ordering information
4	Limiting values2
5	Thermal characteristics4
6	Isolation characteristics
7	Characteristics5
8	Package outline
9	Revision history8
10	Legal information9
10.1	Data sheet status
10.2	Definitions9
10.3	Disclaimers
10.4	Trademarks9
11	Contact information9

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